



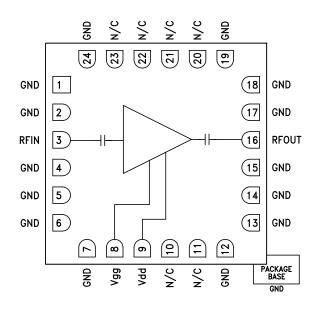
GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

Typical Applications

This HMC772LC4 is ideal for:

- Wideband Communication Systems
- Surveillance Systems
- · Point-to-Point Radios
- · Point-to-Multi-Point Radios
- · Military & Space
- Test Instrumentation

Functional Diagram



Features

Noise Figure: 1.8 dB

Gain: 15 dB

Output IP3: +25 dBm

P1dB Output Power: +13 dBm 50 Ohm Matched Input/Output Supply Voltage: +4V @ 45 mA

24 Lead Ceramic 4x4mm SMT Package: 16mm²

General Description

The HMC772LC4 is a GaAs MMIC HEMT Low Noise Wideband Amplifier which operates between 2 and 12 GHz. The amplifier provides 15 dB of gain, 1.8 dB noise figure up to 12 GHz and output IP3 of +25 dBm, while requiring only 45 mA from a +4V supply voltage. The Psat output power of up to +15 dBm enables the LNA to function as a LO driver for many of HIttite's balanced, I/Q or image reject mixers. The HMC772LC4 also features I/Os that are DC blocked and internally matched to 50 Ohms, making it ideal for SMT based high capacity microwave radio applications. The HMC772LC4 is housed in a RoHS compliant 4x4 mm QFN leadless ceramic package.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd = +4V, Idd = 45 mA*

Parameter	Min.	Тур.	Max.	Units
Frequency Range	2 - 12		GHz	
Gain	14	15		dB
Gain Variation over Temperature		0.01		dB / °C
Noise Figure		1.8	2.5	dB
Input Return Loss		15		dB
Output Return Loss		15		dB
Output Power for 1 dB Compression		13		dBm
Output Third Order Intercept (IP3)		25		dBm
Supply Current (Idd) (Vdd = 4V, Vgg = -0.2V Typ.)*		45		mA

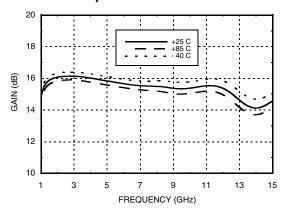
^{*} Adjust Vgg between -1 to 0.3V to achieve Idd = 45mA typical.



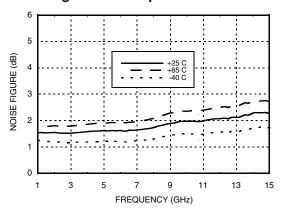


GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

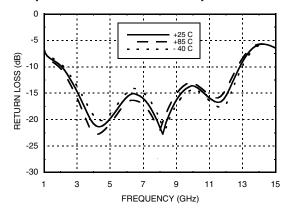
Gain vs. Temperature



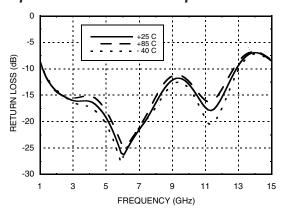
Noise Figure vs. Temperature



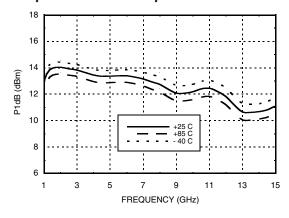
Output Return Loss vs. Temperature



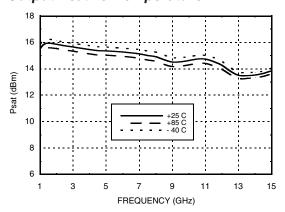
Input Return Loss vs. Temperature



Output P1dB vs. Temperature



Output Psat vs. Temperature

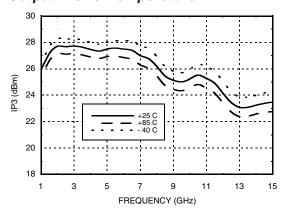




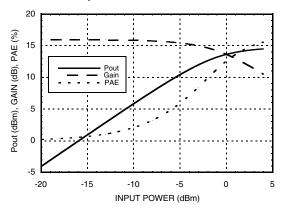


GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

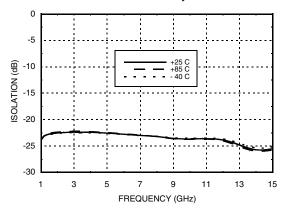
Output IP3 vs. Temperature



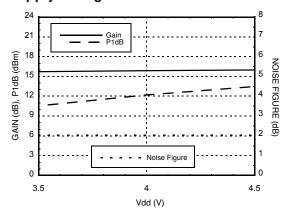
Power Compression @ 12 GHz



Reverse Isolation vs. Temperature



Gain, Noise Figure & Power vs. Supply Voltage @ 12 GHz







GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

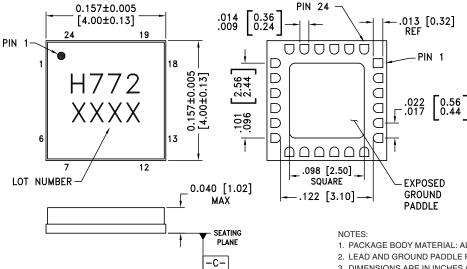
Absolute Maximum Ratings

Drain Bias Voltage	+5V
Drain Bias Current	60 mA
RF Input Power	5 dBm
Gate Bias Voltage	-1 to 0.3 V
Continuous Pdiss (T = 85 °C) (derate 5.8 mW/°C above 85 °C)	0.55 W
Thermal Resistance (Channel to ground paddle)	172 °C/W
Channel Temperature	180 °C
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C



Outline Drawing

BOTTOM VIEW



- 1. PACKAGE BODY MATERIAL: ALUMINA.
- 2. LEAD AND GROUND PADDLE PLATING: GOLD FLASH OVER NICKEL.
- 3. DIMENSIONS ARE IN INCHES (MILLIMETERS).
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05MM DATUM C -
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC772LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H772 XXXX

^[1] Max peak reflow temperature of 260 °C

^{[2] 4-}Digit lot number XXXX



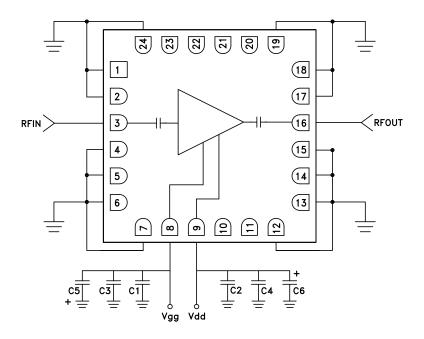


GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 7, 12 - 15, 17 - 19, 24	GND	These pins and ground paddle must be connected to RF/DC ground.	GND =
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN O— —
8	Vgg	Gate control for amplifier. Please follow "MMIC Amplifier Biasing Procedure" application note. See application circuit for required external components.	Vgg ○
9	Vdd	Power Supply Voltage for the amplifier. See application circuit for required external components.	Vdd O—V
10, 11, 20 - 23	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	— —O RFOUT

Application Circuit

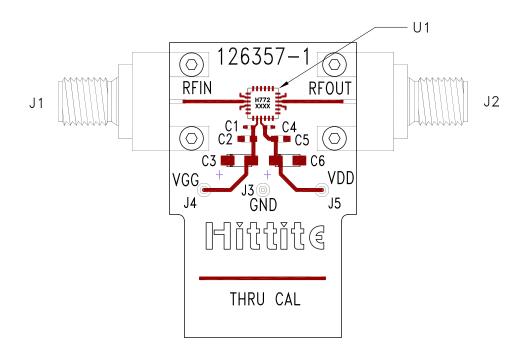






GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

Evaluation PCB



List of Materials for Evaluation PCB 126359 [1]

Item	Description	
J1, J2	PCB Mount 2.92mm K-Connector	
J3 - J5	DC Pin	
C1, C4	100 pF Capacitor, 0402 Pkg.	
C2, C5	1000 pF Capacitor, 0603 Pkg.	
C3, C6	4.7 μF Capacitor, Tantalum	
U1	HMC772LC4 Amplifier	
PCB [2]	126357 Evaluation PCB	

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

^[2] Circuit Board Material: Rogers 4350 or Arlon 25FR

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Development Tools category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

MAAM-011117 MAAP-015036-DIEEV2 EV1HMC1113LP5 EV1HMC6146BLC5A EV1HMC637ALP5 EVAL-ADG919EBZ ADL5363EVALZ LMV228SDEVAL SKYA21001-EVB SMP1331-085-EVB EV1HMC618ALP3 EVAL01-HMC1041LC4 MAAL-011111-000SMB
MAAM-009633-001SMB MASW-000936-001SMB 107712-HMC369LP3 107780-HMC322ALP4 SP000416870 EV1HMC470ALP3
EV1HMC520ALC4 EV1HMC244AG16 MAX2614EVKIT# 124694-HMC742ALP5 SC20ASATEA-8GB-STD MAX2837EVKIT+
MAX2612EVKIT# MAX2692EVKIT# EV1HMC629ALP4E SKY12343-364LF-EVB 108703-HMC452QS16G EV1HMC863ALC4 119197HMC658LP2 EV1HMC647ALP6 ADL5725-EVALZ 106815-HMC441LM1 EV1HMC1018ALP4 UXN14M9PE MAX2016EVKIT
EV1HMC939ALP4 MAX2410EVKIT MAX2204EVKIT+ EV1HMC8073LP3D SIMSA868-DKL SIMSA868C-DKL SKY65806-636EK1
SKY68020-11EK1 SKY67159-396EK1 SKY66181-11-EK1 SKY65804-696EK1 SKY13396-397LF-EVB